

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07763 D T-33-29

2SD687

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)
(DARLINGTON POWER)

SWITCHING APPLICATIONS.
HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS.
POWER AMPLIFIER APPLICATIONS.

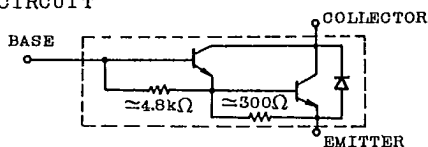
FEATURES :

- . High DC Current Gain
: $h_{FE}=2000$ (Min.) ($V_{CE}=2V, I_C=1A$)
- . Low Saturation Voltage
: $V_{CE(sat)}=1.5V$ (Max.) ($I_C=2A$)

MAXIMUM RATINGS ($T_a=25^\circ C$)

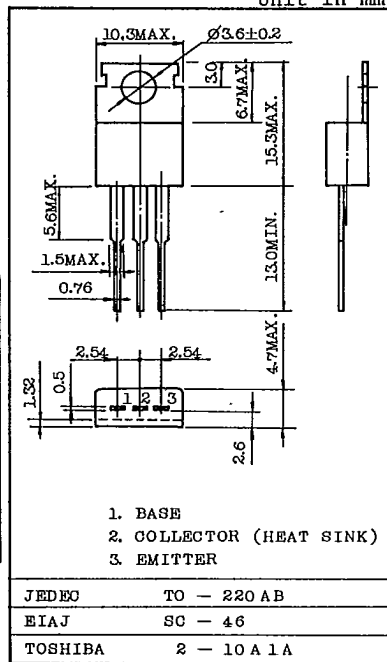
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	3	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	25	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

EQUIVALENT CIRCUIT



INDUSTRIAL APPLICATIONS

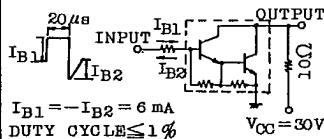
Unit in mm



Mounting Kit No. AC75
Weight : 1.9g

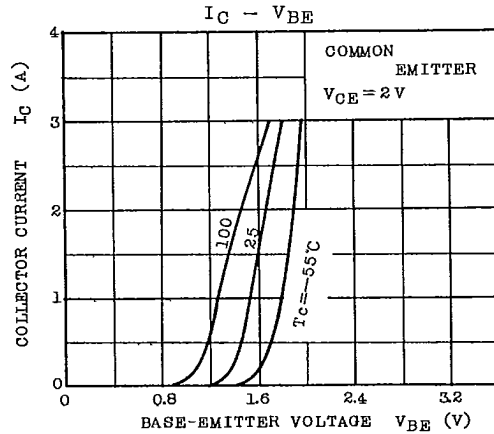
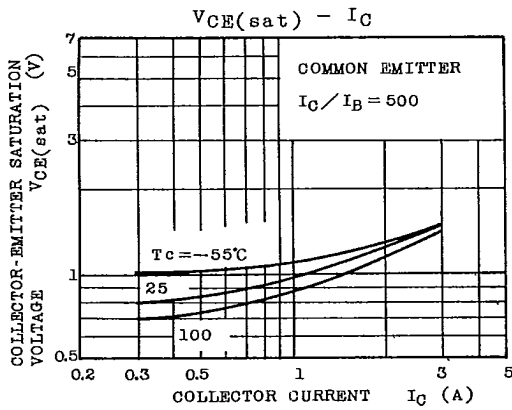
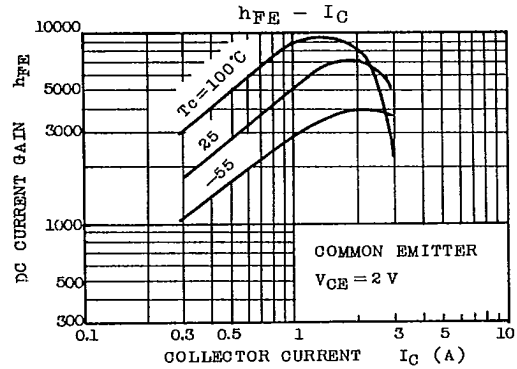
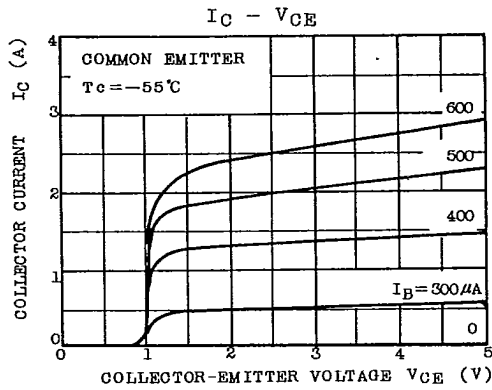
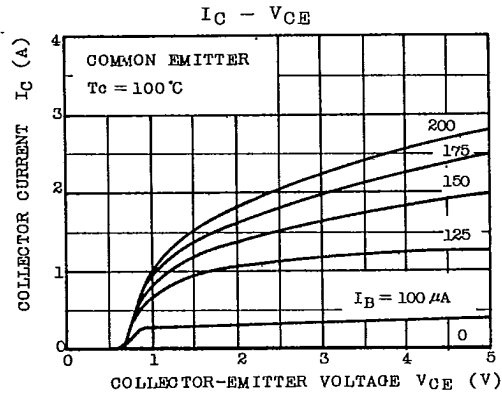
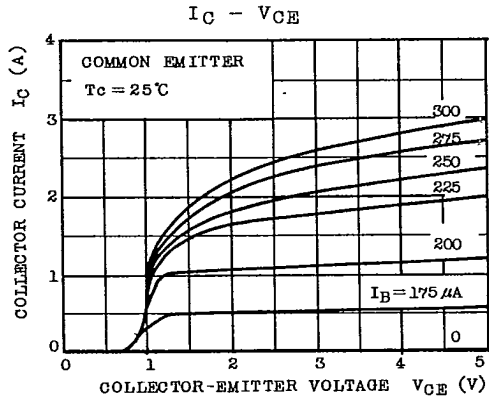
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=60V, I_E=0$	-	-	20	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	2.5	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=25mA, I_B=0$	40	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=1A$	2000	-	-	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=3A$	1000	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	-	-	1.5	V
	Base-Emitter	$V_{BE(sat)}$	-	-	2.0	
Switching Time	Turn-on Time	t_{on}	-	0.1	-	μs
	Storage Time	t_{stg}	-	1.0	-	
	Fall Time	t_f	-	0.2	-	



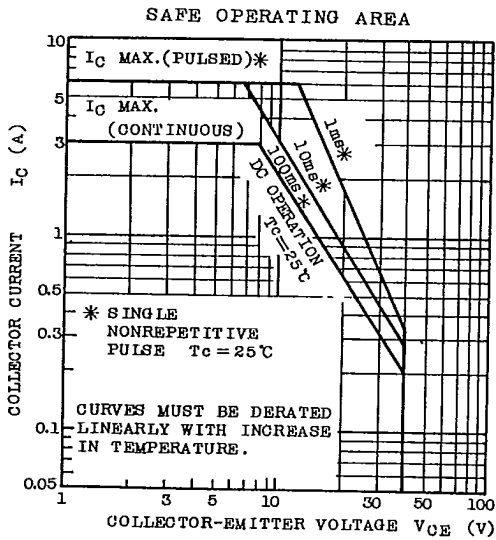
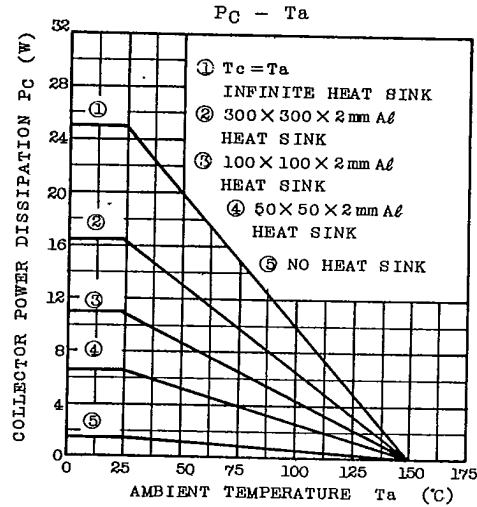
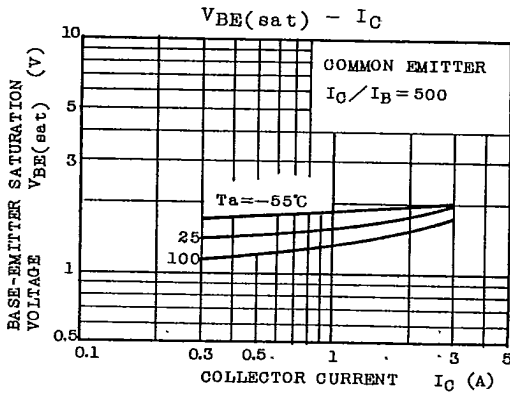
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